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(54) **METHODS FOR PRODUCING POLYSILICON RESISTORS**

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(58) **Field of Classification Search**

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See application file for complete search history.

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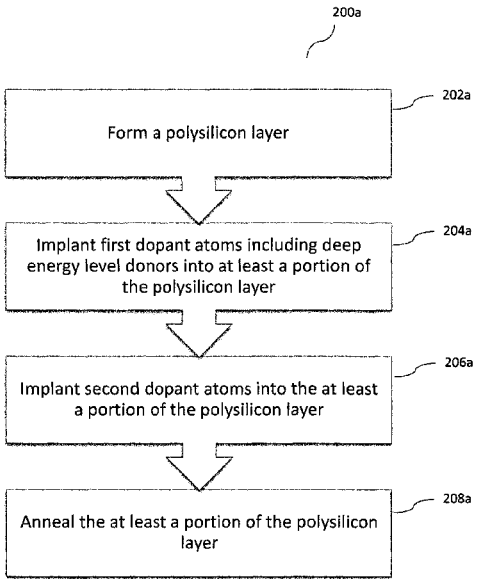
(57) **ABSTRACT**

A method for producing a polysilicon resistor device may include: forming a polysilicon layer; implanting first dopant atoms into at least a portion of the polysilicon layer, wherein the first dopant atoms include deep energy level donors; implanting second dopant atoms into said at least a portion of said polysilicon layer; and annealing said at least a portion of said polysilicon layer.

17 Claims, 10 Drawing Sheets